

GaN	d(A)	Int	h	k	l
Gallium Nitride	2.762	56	1	0	0
	2.593	45	0	0	2
	2.437	100	1	0	1
	1.891	19	1	0	2
	1.5945	31	1	1	0
Rad.: CuK α 1 λ : 1.540598 Filter: Graph Mono d-sp: Diff.	1.4649	27	1	0	3
Cut off: 3.0 Int.: Diffract. I/lor.:	1.3809	4	2	0	0
Ref: Balkas, C., Basceri, C., Davis, R., Powder Diffraction, 10, 266 (1995)	1.3582	22	1	1	2
	1.3345	12	2	0	1
	1.2964	3	0	0	4
	1.2186	3	2	0	2
Sys.: Hexagonal S.G.: P6 ₃ mc (186)	1.1737	2	1	0	4
a: 3.18907(8) b: c: 5.1855(2) A: C: 1.6260	1.0790	7	2	0	3
α : β : γ : Z: 2 mp:	1.0438	3	2	1	0
Ref: Ibid.	1.0234	8	2	1	1
	1.0059	5	1	1	4
	.9709	6	1	0	5
	.9683	5	2	1	2
Dx: 6.088 Dm: SS/FOM: F ₂₃ = 101 (.0095 , 24)	.9452	1	2	0	4
	.9207	4	3	0	0
Color: Off-white	.8936	8	2	1	3
Prepared from molten Ga at 975 C reacted with flowing N H3 (400 sccm) and rapidly cooled. S Zn type. Silicon used as an internal stand. PSC: hP4. To replace 2-1078. Mwt: 83.73.	.8676	4	3	0	2
Volume[CD]: 45.67.	.8644	2	0	0	6

